TOSHIBA Transistor Silicon NPN Epitaxial Type

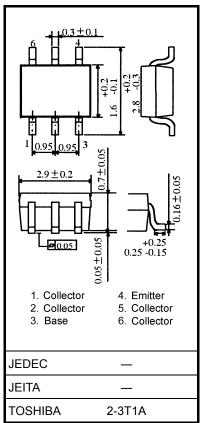
# **TPC6502**

High-Speed Switching Applications DC/DC Converter Applications Strobe Applications

- High DC current gain:  $h_{FE}$  = 400 to 1000 (I<sub>C</sub> = 0.3 A)
- Low collector-emitter saturation voltage: V<sub>CE (sat)</sub> = 0.14 V (max)
- High-speed switching: t<sub>f</sub> = 120 ns (typ.)

Characteristic		Symbol	Rating	Unit	
Collector-base voltage		V <sub>CBO</sub>	100	V	
Collector-emitter voltage		V <sub>CEX</sub>	80	V	
Collector-emitter voltage		V <sub>CEO</sub>	50	V	
Emitter-base voltage		V <sub>EBO</sub>	7	V	
Collector current	DC	Ic	3.0	•	
	Pulse	I <sub>CP</sub>	5.0	A	
Base current		Ι <sub>Β</sub>	300	mA	
Collector power dissipation	DC	D <sub>-</sub> (Note 1)	0.8	w	
	t = 10 s	- P <sub>C</sub> (Note 1) -	1.6		
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	

### Absolute Maximum Ratings (Ta = 25°C)



Weight: 0.01 g (typ.)

Note 1: Mounted on an FR4 board (glass-epoxy; 1.6 mm thick; Cu area, 645 mm<sup>2</sup>)

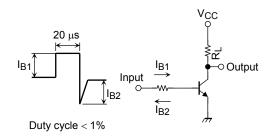
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit: mm

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

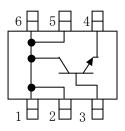
**Electrical Characteristics (Ta = 25°C)** 

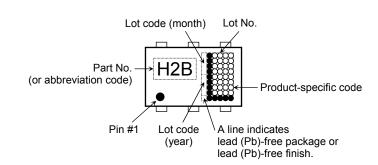
Characteristic		Symbol	Test Condition	Min	Тур.	Мах	Unit
Collector cutoff current		I <sub>CBO</sub>	$V_{CB} = 100 \text{ V}, \text{ I}_{E} = 0$			100	nA
Emitter cutoff current		I <sub>EBO</sub>	$V_{EB} = 7 V, I_C = 0$	_	_	100	nA
Collector-emitter breakdown voltage		V (BR) CEO	$I_{C} = 10 \text{ mA}, I_{B} = 0$	50		_	V
DC current gain		h <sub>FE</sub> (1)	$V_{CE} = 2 V, I_C = 0.3 A$	400		1000	
		h <sub>FE</sub> (2)	$V_{CE} = 2 V, I_C = 1 A$	200		_	
Collector-emitter saturation voltage		V <sub>CE (sat)</sub>	$I_{C} = 1 \text{ A}, I_{B} = 20 \text{ mA}$			0.14	V
Base-emitter saturation voltage		V <sub>BE (sat)</sub>	$I_{C} = 1 \text{ A}, I_{B} = 20 \text{ mA}$			1.10	V
Collector output capacitance		C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		13	_	pF
Switching time	Rise time	tr	See Figure 1 circuit diagram.		40	_	ns
	Storage time	t <sub>stg</sub>	$V_{CC} \simeq 30 \text{ V}, \text{ R}_{L} = 30 \Omega$		500	_	
	Fall time	t <sub>f</sub>	$I_{B1} = -I_{B2} = 33.3 \text{ mA}$		120	_	





## **Circuit Configuration**



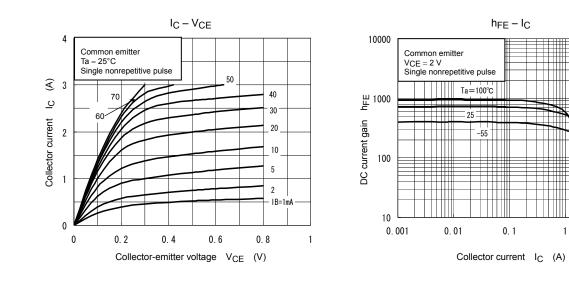


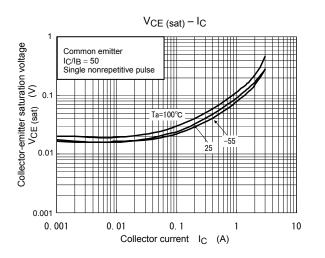
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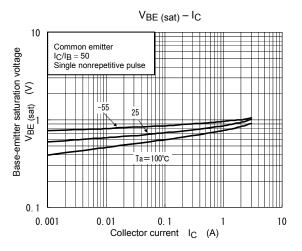
Marking

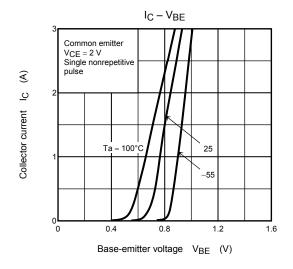
# **TOSHIBA**

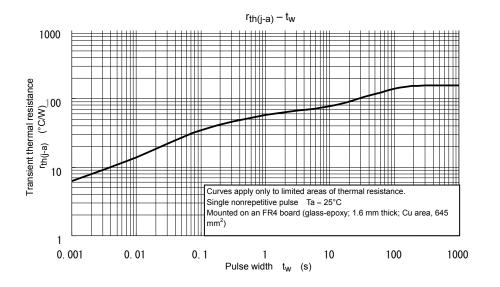
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Safe Operating Area 10 100 Ic max (p 10 ו 10 us\* 10 s4 100 ms<sup>.</sup> E Collector current IC 1 ++++ DC operation Ta = 25°C \*: Single nonrepetitive pulse Ta = 25°C Note that the curves for 100 ms, 10 s and DC operation will be different when the devices are not mounted on an FR4 board (glass-epoxy; 1.6 mm thick; Cu area, 645 mm<sup>2</sup>). These characteristic curves must be derated linearly with increase in temperature. 0.1 0.01 0.1 100 10 1 Collector-emitter voltage  $V_{CE}$  (V)

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